

# SSCN9018GS6

## **SSCN9018GS6**

### **NPN Switching Transistor**

#### $\triangleright$ Features

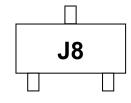
VCB	VCE	VEB	IC
30V	15V	5V	50mA

### Description $\succ$

The NPN Transistor is designed for use in linear and switching

### 3 - Collector 1 - Base 0 0 -0 2 - Emitter

### **Circuit Diagram**



Marking (Top View)

applications. The device is housed in the SOT-23 package,						
which	is	designed	for	telephony	and	professional
commur	nicat	tion equipme	ent.			

General purpose switching and amplification

Telephony and professional communication equipment

### Ordering Information $\geq$

Applications

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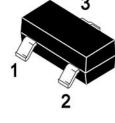
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Device	Package	Shipping
SSCN9018GS6	SOT-23	3000/Reel

# 3

Pin configuration

 $\triangleright$ 



<u>SOT-23</u>



# SSCN9018GS6

### > Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	30	V
Collector- Emitter Voltage	V <sub>CEO</sub>	15	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	V
Collector Current-Continuous	lc	50	mA
Collector Power Dissipation	Pc	200	mW
Junction Temperature	TJ	-55 to 150	°C
Storage Temperature	T <sub>STG</sub>	-55 to 150	°C

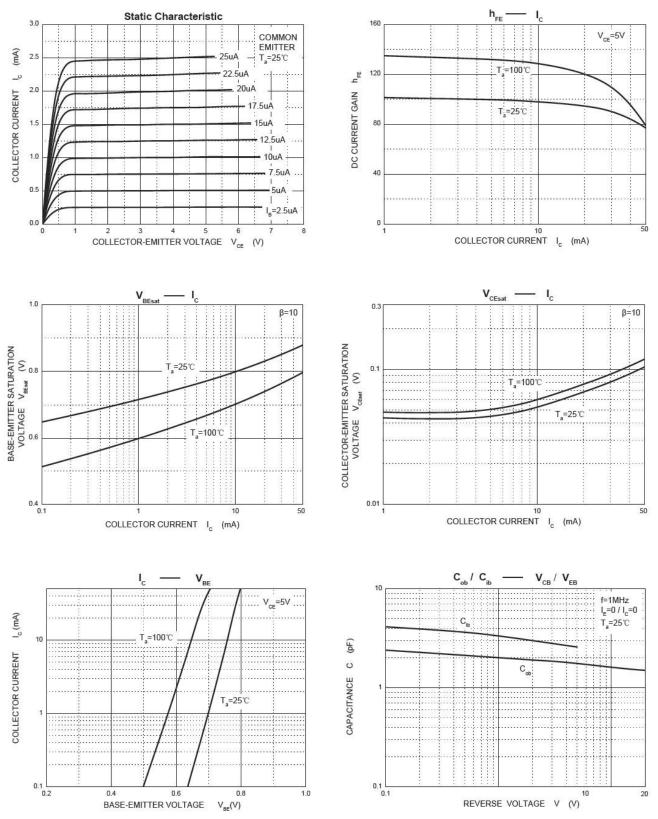
### > Electrical Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	I <sub>C</sub> =100uA,I <sub>E</sub> =0	30			V
Collector-emitter Breakdown Voltage	BV <sub>CEO</sub>	I <sub>C</sub> =1mA,I <sub>B</sub> =0	15			V
Emitter -Base Breakdown Voltage	BV <sub>EBO</sub>	I <sub>E</sub> =100uA,I <sub>C</sub> =0	6			V
Collector Cutoff Current	I <sub>СВО</sub>	V <sub>CB</sub> =12V, I <sub>E</sub> =0			0.05	μA
Collector Cutoff Current	I <sub>CEO</sub>	V <sub>CE</sub> =12V,I <sub>B</sub> =0			0.1	μA
Emitter Cutoff Current	Іево	V <sub>EB</sub> =3V,I <sub>C</sub> =0			0.1	μA
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V,I <sub>C</sub> =1mA	70		200	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	Ic=10mA,I <sub>B</sub> =1mA			0.5	V
Base-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	Ic=10mA,I <sub>B</sub> =1mA			1.4	V
Transition frequency	fT	V <sub>CE</sub> =5V,I <sub>C</sub> =5mA f=400MHz		800		MHz



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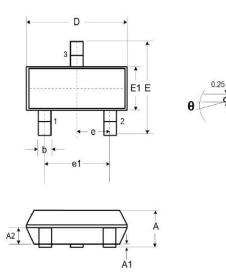
### > Typical Performance Characteristics ( $T_A=25^{\circ}C$ unless otherwise noted)





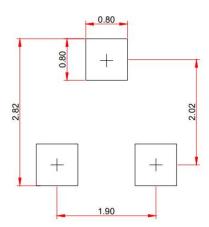


## Package Information



DIM	Millimeters				
DIN	Min.	Тур.	Max.		
Α	0.89	-	1.12		
A1	0.01	-	0.10		
A2	0.88	0.95	1.02		
b	0.30	-	0.51		
С	0.08	-	0.18		
D	2.80	2.90	3.04		
E	2.10	2.37	2.64		
E1	1.20	1.30	1.40		
е	1.90				
e1	0.95				
L	0.40	0.50	0.60		
L1	0.55				
N	3				
θ	0°	-	8°		

Recommended Pad outline (Unit: mm)



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